# Using the UCC28610EVM-474

# **User's Guide**



Literature Number: SLUU383B November 2009-Revised May 2011



# UCC28610EVM-474 25-W Universal Off-Line Flyback Converter

#### 1 Introduction

The UCC28610EVM-474 evaluation module is a 25-W off-line Discontinuous Mode (DCM) flyback converter providing 12 V at 2.1-A maximum load current, operating from a universal AC input. The module is controlled with the UCC28610 Green-Mode Flyback Controller which uses a cascoded architecture that allows fully integrated current control without an external sense resistor. The converter maintains discontinuous mode operation over the entire operating range. This innovative approach results in efficiency, reliability, and system cost improvements over a conventional flyback.

## 2 Description

This evaluation module uses the UCC28610 Green-Mode Flyback Controller (TI Literature Number SLUS888) in a 25-W DCM flyback converter that exceeds Energy Star™ EPS version 2.0 for efficiency during active load and no-load power consumption. The input accepts a voltage range of 85 V<sub>AC</sub> to 265 V<sub>AC</sub>. The output provides a regulated output voltage of 12 V<sub>DC</sub> at a load current of up to 2.1 A. The converter will transition through three operating modes: green mode (GM), amplitude modulation (AM), and frequency modulation (FM), depending upon the power level and FB current. In FM mode, the on-time is fixed, resulting in a fixed peak primary current at each cycle, and the switching frequency is increased with increasing load. In AM mode, the switching frequency is fixed at 30 kHz and the peak primary current is modulated with the on-time as with any typical PWM controller. Green mode operation at light load consists of burst packets of 30-kHz pulses with a fixed on-time and peak primary currents of 33% of the maximum programmed level. Low system parts count and built in advanced protection features result in a cost-effective solution that meets stringent world-wide energy efficiency requirements.

This user's guide provides the schematic, component list, assembly drawing, art work, and test set up necessary to evaluate the UCC28610 in a typical off-line converter application.



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# 2.1 Applications

The UCC28610 is suited for use in isolated off-line systems requiring high efficiency and advanced fault protection features including:

- AC/DC Adaptors that have a Peak Power Output of 12 W to 65 W
- Housekeeping and Auxiliary Power Supplies
- Off-line Battery Chargers
- Consumer Electronics (DVD players, set-top boxes, gaming, printers, etc.)

#### 2.2 Features

The UCC28610EVM-474 features include:

- Isolated 25 W, 12-V output
- Universal Off-Line Input Voltage Range
- Exceeds Energy Star™ EPS Version 2.0 Requirements for Active Load Efficiency and No-Load Power Consumption
- Cascoded Configuration Allows Fully Integrated Current Control Without an External Sense Resistor
- · Multiple Operating Modes for Optimum Efficiency Over entire Operating Range
- Over Current Protection to Limit RMS Input and Output Current
- Timed overload with Shutdown/Retry Response
- · Opto-Less Output Overload Protection

#### **CAUTION**

High voltage levels are present on the evaluation module whenever it is energized. Proper precautions must be taken when working with the EVM. The large bulk capacitor, C9, and the output capacitors, C15 and C16, must be completely discharged before the EVM can be handled. Serious injury can occur if proper safety precautions are not followed.



# 3 Electrical Performance Specifications

Table 1. UCC28610EVM-474 Electrical Performance Specifications

PARAMETER		CONDITIONS		NOM	MAX	UNITS
INPUT C	CHARACTERISTICS		1		1	
V <sub>IN</sub>	Input voltage		85		265	VRMS
I <sub>IN</sub>	Input current	$V_{IN} = 115 V_{RMS}, I_{OUT} = max$		0.3		Α
		V <sub>IN</sub> = 115 V <sub>RMS</sub> , I <sub>OUT</sub> = 0 A		0.03		Α
$V_{\text{UVLO}}$	Brown out	I <sub>OUT</sub> = max		72		V
OUTPU	T CHARACTERISTICS					
V <sub>OUT</sub>	Output voltage	$V_{IN}$ = min to max, $I_{OUT}$ = min to max	10.8	12	13.2	V
V <sub>ripple</sub>	Output voltage ripple	$V_{IN} = 115 V_{RMS}, I_{OUT} = max$		80	120	mVpp
I <sub>OUT</sub>	Output current	V <sub>IN</sub> = min to max	0		2.1	Α
I <sub>OCP</sub>	Output over current inception point	V <sub>IN</sub> = max		3		А
$V_{OVP}$	Output OVP	I <sub>OUT</sub> = min to max			16	V
	Transient response voltage over shoot	I <sub>OUT</sub> = min to max		500		mV
SYSTEM	I CHARACTERISTICS				'	
f <sub>SW</sub>	Switching frequency		26.3		140.4	kHz
h <sub>PEAK</sub>	Peak efficiency	V <sub>IN</sub> = 115 V <sub>RMS</sub> , I <sub>OUT</sub> = 1.05 A		85.7		%
	No load power consumption	$V_{IN} = 115 V_{RMS}$		67		mW
		$V_{IN} = 230 V_{RMS}$		107		IIIVV
	Operating temperature range	$V_{IN}$ = min to max, $I_{OUT}$ = min to max		25		°C
MECHA	NICAL CHARACTERISTICS	•	* '	-		
Width	Dimensions			2.3		
Length				3.5		inches
Height		Component height			1	



# 4 Schematic/Revision Code Placement

**NOTE:** For revision A versions of the evaluation module, please refer to Appendix A of this user's guide for the schematic, list of materials and board layout. The EVM revision code can be found on the lower right corner of the top side of the board, as shown in Figure 1.

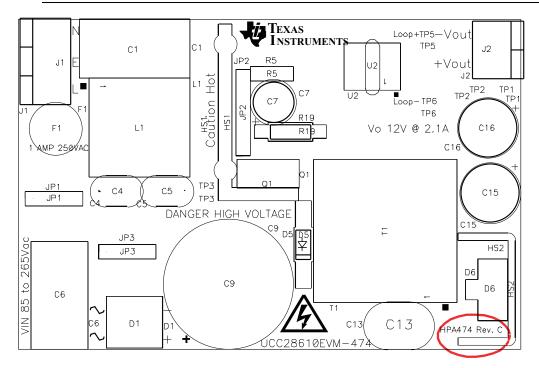


Figure 1. Placement of Revision Code for the Evaluation Module.



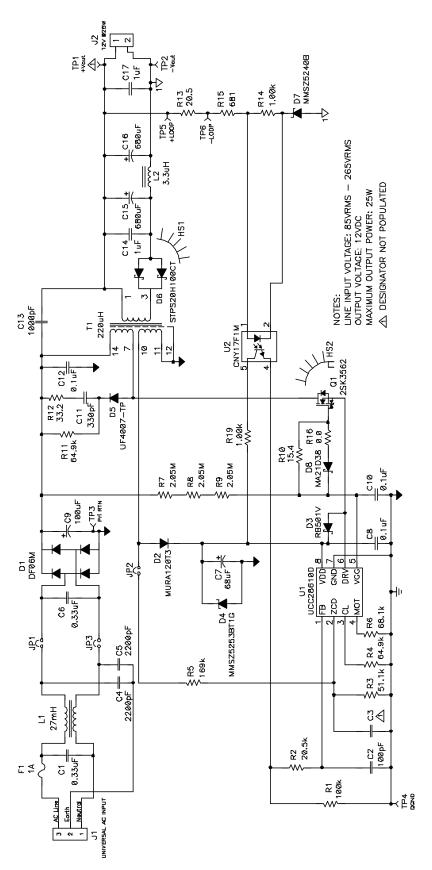


Figure 2. UCC28610EVM-474 Schematic



## 4.1 Circuit Description

A brief description of the circuit elements follows:

- Diode bridge D1, input capacitor C9, transformer (a.k.a. flyback inductor) T1, HV MOSFET Q1, UCC28610 controller U1, Schottky rectifier D6, Output capacitors C15 and C16 form the power stage of the converter. Note that the UCC28610 U1 is part of the power stage. This is because the DRV and GND pins carry the full peak primary side current of the converter.
- Capacitors C12, C14, and C17 filter the high frequency noise directly across the electrolytic input and output capacitors.
- The input EMI filter is made up of X2 capacitors, C1 and C6, and common mode inductor L1 and Y2 capacitors, C4 and C5. Excessive surge current protection is provided by a slow blow fuse, F1.
- Resistor R11, capacitor C11, and diode D5 make up the primary side voltage clamp for the HV MOSFET. The clamp prevents the drain voltage on Q1 from exceeding its maximum rating. The integrated snubber, composed of R12 and C11, reduces the ringing on the primary side windings that might inadvertently trigger the zero current detection circuit in the device.
- Resistors R7, R8, and R9 supply start up bias current to the VGG shunt regulator. Schottky diode D3 is required to provide initial start up to VDD from VGG at start up.
- Operating bias to the controller is provided by the auxiliary winding on T1, diode D2, and bulk capacitor C7. The zener diode, D4, maintains the bias voltage on VDD below the absolute maximum rating at full load.
- Gate drive circuitry is composed of gate drive resistor R10, used for damping oscillations during turn
  on. Resistor R16 and diode D8 are required to provide a current path at turn off because the gate is
  shorted to the source of the HV MOSFET during each switching cycle. For circuits that experience high
  ringing on VGG at turn off, R16 can be replaced with a ferrite bead.
- Capacitors C8 and C10 are decoupling capacitors which should always be good quality low ESR/ESL type capacitors placed as close to the device pins as possible and returned directly to the device ground reference.
- C13 filters the common mode noise between the primary and secondary sides.
- Inductor L2, with capacitor C16, reduces the output voltage ripple.
- Resistors R5 and R3 program the over voltage threshold. Capacitor C3 can be used to add a small delay to ZCD, to align the turn on time of the primary switch with the resonant valley of the primary winding.
- Resistor R6 programs the maximum on time of the HV MOSFET.
- Resistor R4 sets the maximum value for the peak primary current.
- Resistor R2 and capacitor C2 provide a filter for the FB signal while resistor R1 ensures that the
  optocoupler emitter current can go to 0A. Resistor R19 provides a non-intrusive point to monitor the FB
  by measuring the voltage drop across R19.
- The simple output voltage feedback loop is composed of zener diode D7, resistors R14 and R15, and the optocoupler U2. Using an opto with a low CTR provides better noise immunity. Resistor R13 is used as an injection point for small signal frequency response testing.



EVM Test Set Up www.ti.com

## 5 EVM Test Set Up

Figure 2 shows the equipment set up when measuring the input power consumption during no load. Note the addition of the  $10-\Omega$  shunt resistor in Figure 3. During the no-load test, the power analyzer should be set for long averaging in order to include several cycles of operation and an appropriate current scale factor for using the external shunt must be used. Figure 3 shows the basic test set up recommended to evaluate the UCC28610EVM-474 with a load.

# **WARNING**

High voltages that may cause injury exist on this evaluation module (EVM). Please ensure all safety procedures are followed when working on this EVM. Never leave a powered EVM unattended.

# 5.1 Test Equipment

See Figure 3 and Figure 4 for recommended test set ups.

- AC Input Source: The input source shall be an isolated variable AC source capable of supplying between 85 V<sub>RMS</sub> and 265 V<sub>RMS</sub> at no less than 30 W and connected as shown in Figure 3 and Figure 4. For accurate efficiency calculations, a power meter should be inserted between the neutral line of the AC source and the Neutral terminal of the EVM. For highest accuracy, connect the voltage terminals of the power meter directly across the Line and Neutral terminals of the EVM.
- Load: For the output load, a programmable electronic load set to constant current mode and capable
  of sinking 0 to 3 A<sub>DC</sub> at 12 V<sub>DC</sub> shall be used. For highest accuracy, V<sub>OUT</sub> can be monitored by
  connecting a DC voltmeter, DMM V<sub>1</sub>, directly across the +Vout and –Vout terminals as shown in
  Figure 3 and Figure 4. A DC current meter, DMM A<sub>1</sub>, should be placed in series with the electronic
  load for accurate output current measurements.
- **Power Meter:** The power analyzer shall be capable of measuring low input current, typically less than 10 mA, and a long averaging mode if low power standby mode input power measurements are to be taken. An example of such an analyzer is the Voltech PM100 Single Phase Power Analyzer. To measure the intermittent bursts of current and power drawn from the line during no-load operation, an external 10-Ω shunt, with a current scale factor of 10 A/V, was used at a high sample rate over an extended period of time in order to display the averaged results (refer to Figure 3).
- Multimeters: Two digital multimeters are used to measure the regulated output voltage (DMM V<sub>1</sub>) and load current (DMM A<sub>1</sub>).
- Oscilloscope: A digital or analog oscilloscope with a 500-MHz scope probe is recommended.
- Fan: Forced air cooling is not required.
- Recommended Wire Gauge: a minimum of AWG18 wire is recommended. The wire connections between the AC source and the EVM, and the wire connections between the EVM and the load should be less than two feet long.



www.ti.com EVM Test Set Up

# 5.2 Recommended Test Set Up for Operation Without a Load

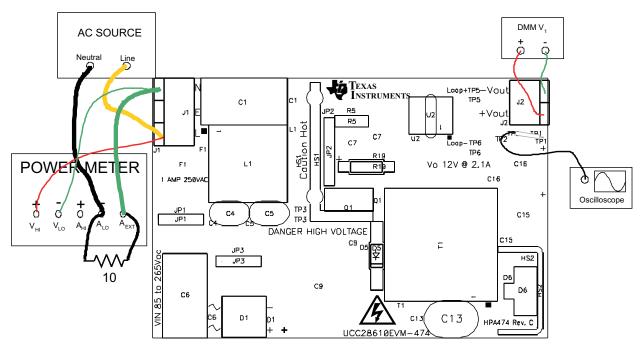


Figure 3. UCC28610EVM-474 Recommended Test Set Up Without a Load

# 5.3 Recommended Test Set Up for Operation With a Load

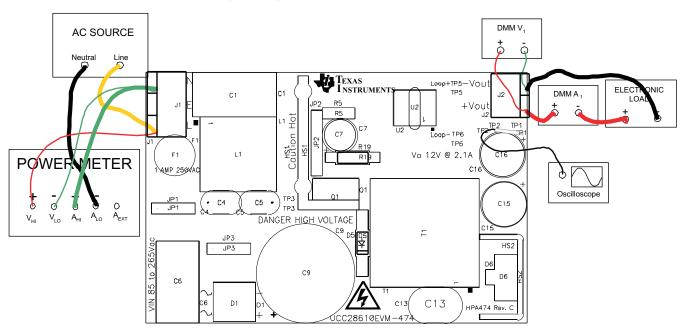


Figure 4. UCC28610EVM-474 Recommended Test Set Up With a Load



EVM Test Set Up www.ti.com

# 5.4 List of Test Points

# **Table 2. Test Point Functional Description**

TEST POINT	NAME	DESCRIPTION	
TP1	+Vout	Output voltage of EVM; this designator is not populated with a pin in order to facilitate tip and barrel output ripple voltage measurements.	
TP2	-Vout	Return of the output of the EVM, secondary side GND reference.	
TP3	Pwr RTN	Primary side power ground	
TP4	QGND	Primary side signal ground	
TP5	+LOOP	Loop injection point, EVM output	
TP6	-LOOP	Loop injection point	
J1-1	Neutral	Neutral input from the AC source	
J1-2	Earth	Earth reference from the AC source	
J1-3	AC Line	Line input from AC source	
J2-1	+Vout	Positive output terminal of the EVM to the load	
J2-2	-Vout	Return connection of the EVM output to the load	



www.ti.com Test Procedure

#### 6 Test Procedure

All tests should use the set up as described in Section 5 of this user's guide. The following test procedure is recommended primarily for power up and shutting down the evaluation module. Never leave a powered EVM unattended for any length of time.

## 6.1 Applying Power to the EVM

- 1. Set up the EVM as shown in Section 5 of this user's guide
  - (a) If no-load input power measurements are to be made, set the power analyzer to long averaging and external shunt mode. Insert a shunt, such as a  $10-\Omega$  resistor as shown in Figure 3, in series with the Neutral terminal of the EVM. Set the appropriate current scale on the power analyzer.
  - (b) For operation with a load, as shown in Figure 4, set the electronic load to constant current mode to sink 0 A.
- 2. Prior to turning on the AC source, set the voltage to between 85  $V_{AC}$  and 265  $V_{AC}$ .
- 3. Turn on the AC source.
- 4. Monitor the output voltage on DMM V<sub>1</sub>.
- 5. Monitor the output current on DMM A<sub>1</sub>.
- 6. The EVM is now ready for testing.

## 6.2 No-Load Power Consumption

- 1. Use the test set up shown in Figure 3.
  - (a) Set the power analyzer to external shunt mode.
  - (b) Set the appropriate current scale factor for using an external shunt on the power analyzer. A 10-Ω shunt scales at 10,000 mV/A for the PM100 Voltech.
  - (c) Set the power analyzer long averaging time to include several cycles of operation. The PM100 Voltech should be set to a long averaging time of 10 or more for accurate burst mode measurements.
- 2. Apply power to the EVM per Section 6.1.
- 3. Monitor the input power on the power analyzer while varying the input voltage.
- Make sure the input power is off and the bulk capacitor and output capacitors are completely discharged before handling the EVM.



Test Procedure www.ti.com

# 6.3 Output Voltage Regulation and Efficiency

- 1. For load regulation:
  - (a) Use the test set up shown in Figure 4.
    - Be sure to remove the external shunt from the power analyzer and set the analyzer to normal mode (not long averaging).
  - (b) Set the AC source to a constant voltage between 85  $V_{AC}$  and 265  $V_{AC}$ .
  - (c) Apply power to the EVM per Section 6.1.
  - (d) Vary the load current from 0 A up to 2.1 A, as measured on DMM A<sub>1</sub>.
  - (e) Observe that the output voltage on DMM  $V_1$  remains within 10% of 12  $V_{DC}$ .
- 2. For line regulation:
  - (a) Set the load to sink 2.1 A.
  - (b) Vary the AC source from 85  $V_{AC}$  to 265  $V_{AC}$ .
  - (c) Observe that the output voltage on DMM  $V_1$  remains within 10% of 12  $V_{DC}$ .
- 3. Make sure the input power is off and the bulk capacitor and output capacitors are completely discharged before handling the EVM.

# 6.4 Output Voltage Ripple

- Expose the ground barrel of the scope probe. Insert the tip of the probe into the plated via located on the +Vout pad of the EVM (TP1) and lean the probe so that the exposed ground barrel is resting on the test point on the -Vout pad of the EVM (TP2) for a tip and barrel measurement as shown in the example depicted in Figure 5.
- 2. Apply power to the EVM per Section 6.1.
- 3. Monitor the output voltage ripple on the oscilloscope.

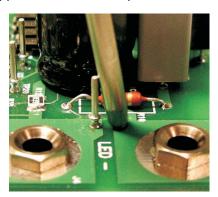


Figure 5. Typical Example of Tip and Barrel Measurement Technique

**NOTE:** This photo was not taken on the UCC28610EVM specifically but serves as a visual aid to perform the test measurement.

#### 6.5 Equipment Shutdown

- 1. Ensure the load is at maximum; this will quickly discharge the output capacitors.
- 2. Turn off the AC source.



# 7 Performance Data and Typical Characteristic Curves

Figure 6 through Figure 23 present typical performance curves for the UCC28610EVM-474.

#### EFFICIENCY vs. LOAD CURRENT

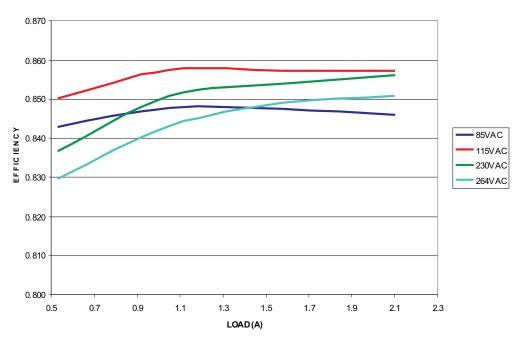


Figure 6. Efficiency as a Function of Load Current and Input Voltage

#### No-Load Power Consumption vs. Line Voltage

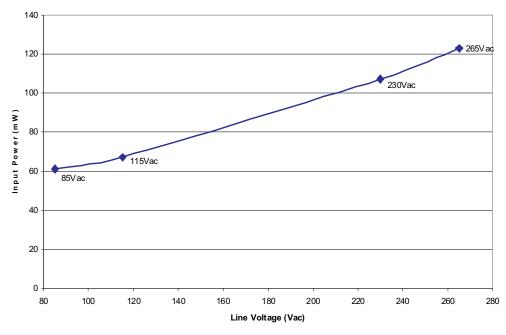


Figure 7. No-Load Input Power as a Function of Input Voltage



#### FB CURRENT vs. DRV CURRENT

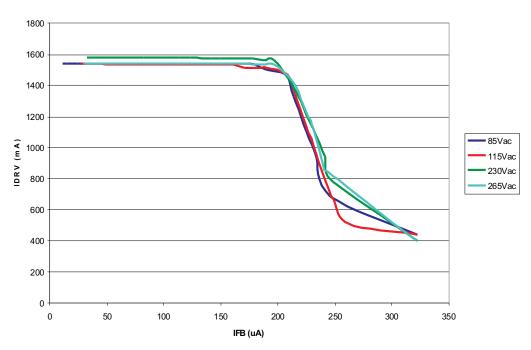


Figure 8. DRV Current as a Function of FB Current

#### FB CURRENT vs. SWITCHING FREQUENCY

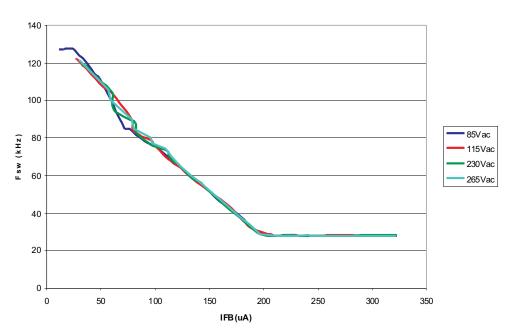


Figure 9. Switching Frequency as a Function of FB Current



#### **OUTPUT VOLTAGE vs LOAD CURRENT**

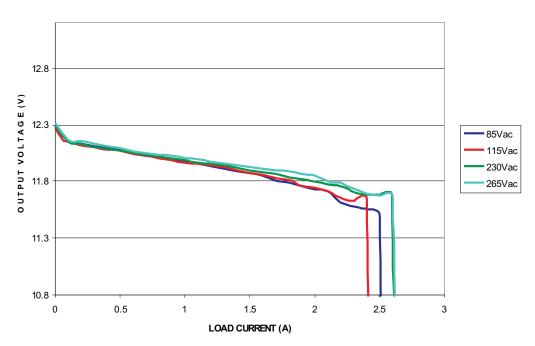


Figure 10. Output Voltage as a Function of Load Current and Line Voltage (Note the shutdown/retry threshold for each line voltage.)

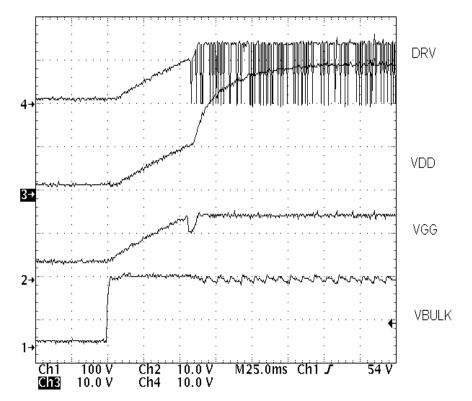


Figure 11. Start-Up Waveform (Input voltage = 115  $V_{AC}$ , full load. Ch.1 = bulk input voltage, 100 V/div., Ch.2 = VGG, 10 V/div., Ch.3 = VDD, 10V/div., Ch.4 = DRV, 10V/div.)



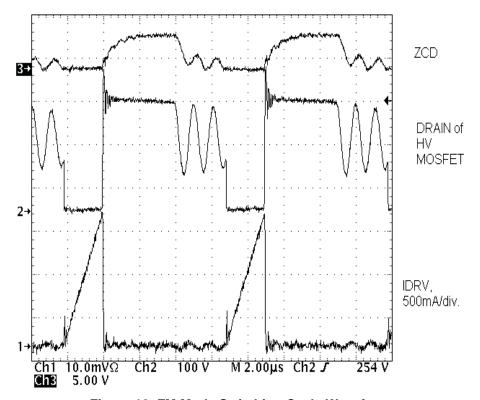


Figure 12. FM Mode Switching Cycle Waveform (Input voltage = 115 V<sub>AC</sub>, full load, f<sub>SW</sub> = 112 kHz. Ch.1 = I<sub>DRV</sub>, 500 mA/div., I<sub>DRV</sub> = 1.53 A, Ch.2 = Drain of HV MOSFET, 100 V/div., Ch.3 = ZCD, 5 V/div.)

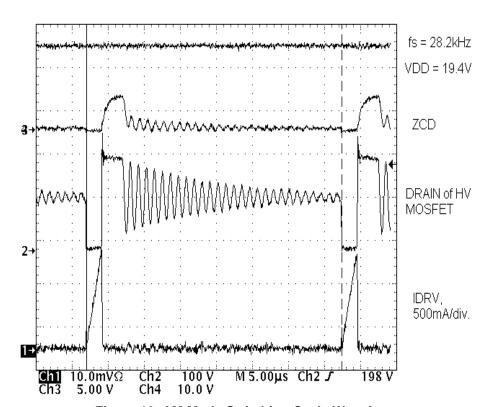


Figure 13. AM Mode Switching Cycle Waveform (Input voltage = 85  $V_{AC}$ , 0.3-A load,  $f_{SW}$  = 28.2 kHz, Ch.1 =  $I_{DRV}$ , 500 mA/div.,  $I_{DRV}$  = 1.1 A, Ch.2 = Drain of HV MOSFET, 100 V/div., Ch.3 = ZCD, 5 V/div., Ch. 4 = VDD, 10 V/div.)



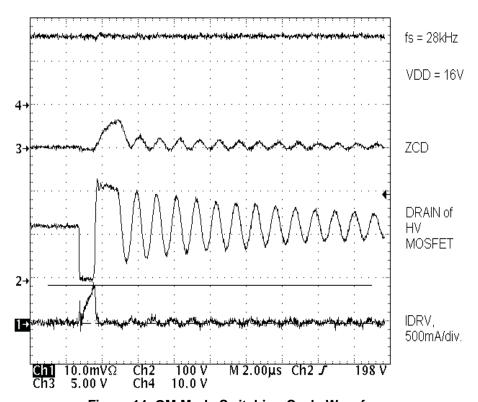


Figure 14. GM Mode Switching Cycle Waveform (Input voltage = 85  $V_{AC}$ , 0-A load,  $f_{SW}$  = 28 kHz, Ch.1 =  $I_{DRV}$ , 500 mA/div.,  $I_{DRV}$  = 440 mA, Ch.2 = Drain of HV MOSFET, 100 V/div., Ch.3 = ZCD, 5 V/div., Ch. 4 = VDD, 10 V/div.)

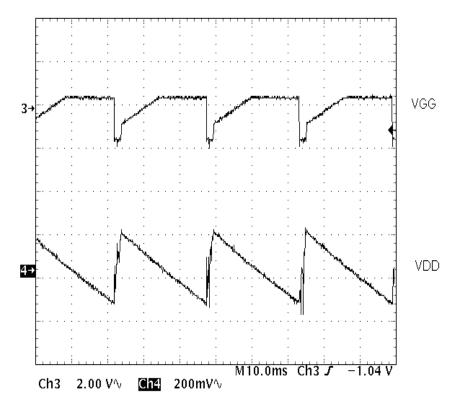


Figure 15. Ripple on VGG and VDD During Green Mode Operation (Ch.3 = VGG, AC coupled, 2 V/div., Ch.4 = VDD, AC coupled, 200 mV/div.)



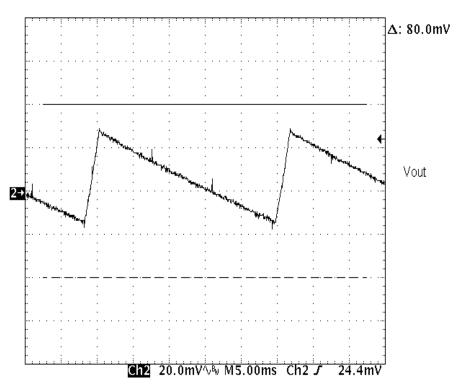


Figure 16. Output Voltage Ripple During Green Mode Operation (Input voltage = 85  $V_{AC}$ , no load. Ch.2 =  $V_{OUT}$ , AC coupled, 20 mV/div.)

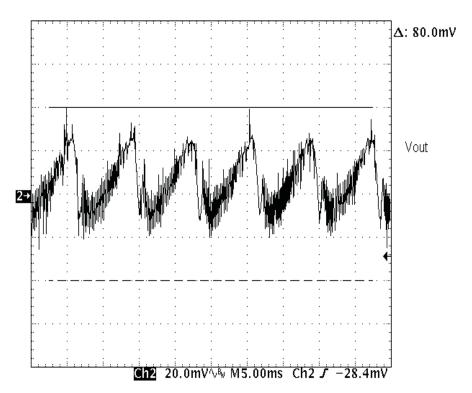


Figure 17. Output Voltage Ripple During Frequency Modulation Mode (Input voltage = 85  $V_{AC}$ , full load. Ch.2 =  $V_{OUT}$ , AC coupled, 20 mV/div.)



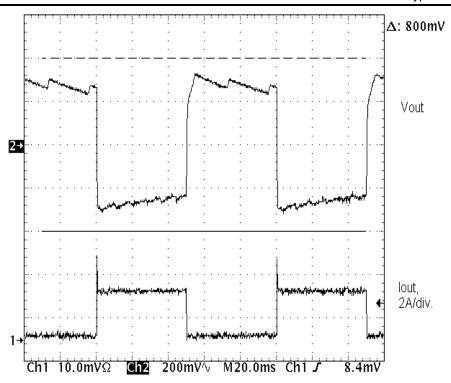


Figure 18. Load Transient, 0% to 100% Load Step (Ch.1 =  $I_{OUT}$ , 2 A/div., Ch.2 =  $V_{OUT}$ , AC coupled, 200 mV/div.)

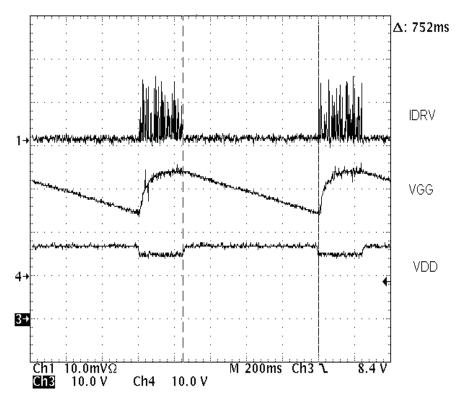


Figure 19. Brown-Out Protection (MOT shutdown/retry response triggered at full load when input voltage dropped to 72.4  $V_{AC}$ . Note the 750-ms  $t_{RETRY}$ . Ch.1 =  $I_{DRV}$ , Ch.3 = VDD, 10 V/div., Ch.4 = VGG, 10 V/div.)



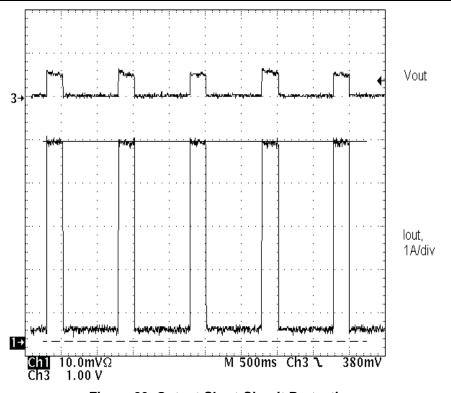


Figure 20. Output Short Circuit Protection (Short circuit maintained on output; note the output current goes to 4.62 A, refer to equation 13 in the data sheet, during the 250-ms delay to overload fault,  $t_{OL}$ , and retries after  $t_{RETRY}$  = 750 ms. Input voltage = 85  $V_{AC}$ . Ch.1 =  $I_{OUT}$ , 1 A/div., Ch. 3 =  $V_{OUT}$ , 1 V/div.)

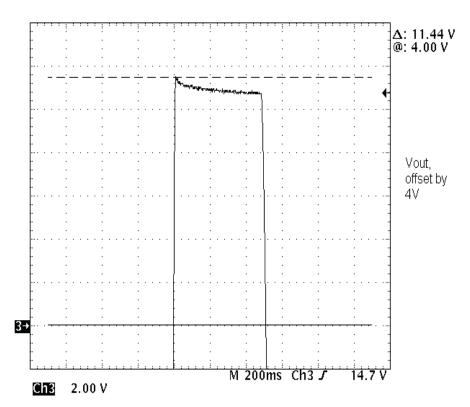


Figure 21. Output Over Voltage Protection (The EVM was tested with an open FB loop, no load. OVP threshold is equal to 15.44 V. Ch.  $3 = V_{OUT}$ , 2 V/div., offset by 4 V.)





Figure 22. Bode Plot (Input voltage = 115  $V_{AC}$ , full load.)

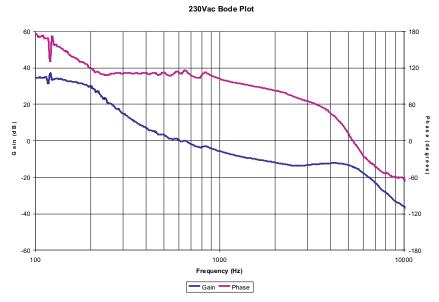


Figure 23. Bode Plot (Input voltage = 230  $V_{AC}$ , full load.)



# 8 EVM Assembly Drawing and Layout

Figure 24 through Figure 26 show the design of the UCC28610EVM-474 printed circuit board.

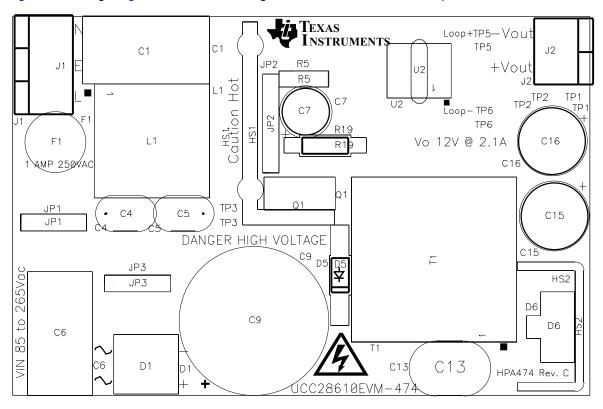


Figure 24. Top Layer Component Placement



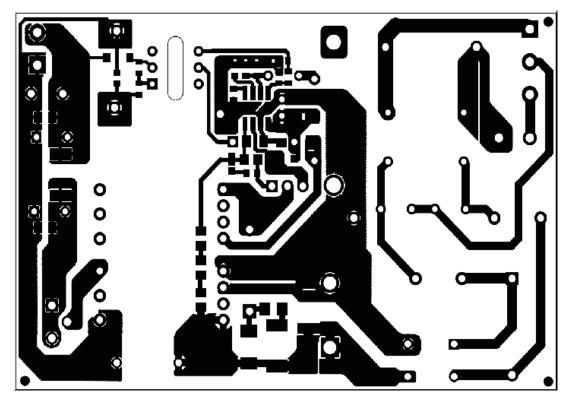


Figure 25. Bottom Layer Routing

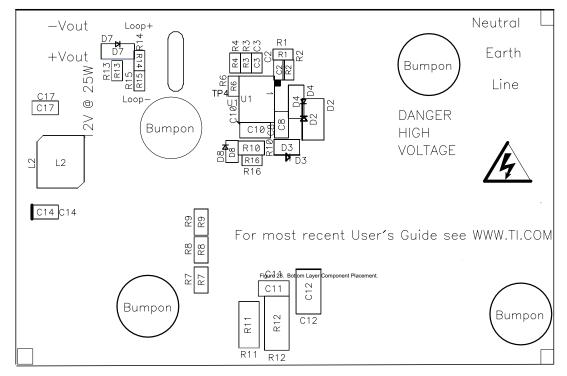


Figure 26. Bottom Layer Component Placement



List of Materials www.ti.com

# 9 List of Materials

# Table 3. List of Materials for UCC28610EVM-474

COUNT	REF DES	DESCRIPTION	PART NUMBER	MFR
2	C1, C6	Capacitor, film, 0.33 $\mu$ F, 275 VAC, X2, ±20%, 0.690 x 0.374 inch	ECQ-U2A334ML	Panasonic
1	C2	Capacitor, ceramic, 100 pF, 50 V, NP0, ±5%, 0603	Std	Std
0	C3	Capacitor, ceramic, not populated, 50 V, NP0, ±5%, 0603	Std	Std
2	C4, C5 (optional)	Capacitor, ceramic, 2200 pF, 250 VAC, X1/Y2, ±20%, 0.315 x 0.200 inch	DE2E3KY222MA2BM01	muRata
1	C7	Capacitor, aluminum electrolytic, 68 µF, 35 V, ±20%, 0.200 inch	EEU-FC1V680	Panasonic
1	C8	Capacitor, ceramic, 0.1 µF, 50 V, X7R, ±10%, 0805	CC0805KRX7R9BB104	Yageo Corporation
1	C9	Capacitor, aluminum electrolytic, 100 μF, 400 VDC, ±20%, 25 x 20 mm	EET-HC2G101BA	Panasonic
1	C10	Capacitor, ceramic, 0.1 µF, 100 V, X7R, ±10%, 1206	Std	Std
1	C11	Capacitor, ceramic, 330 pF, 630 V, C0G, NP0, ±5%, 1206	Std	Std
1	C12	Capacitor, ceramic, 0.1 µF, 630 V, X7R, ±10%, 1812	C4532X7R2J104K	TDK Corporation
1	C13	Capacitor, ceramic disk, 1000 pF, 250 V, Y1/X1, ±20%, 0.394 x 0.315 inch	ECK-ANA102MB	Panasonic
2	C14, C17	Capacitor, ceramic, 1 µF, 25 V, X5R, ±10%, 0805	Std	Std
2	C15, C16	Capacitor, aluminum electrolytic, 680 µF, 25 V, ±20%, 10 x 25 mm	EEU-FM1E681	Panasonic
1	D1	Diode, bridge, 1 A, 600 V	DF06M	Diodes Inc.
1	D2	Diode, ultra fast, 1 A, 200 V, SMA	MURA120T3G	On Semiconductor
1	D3	Diode, schottky, 100 mA, 40 V, SOD-323	RB501V-40TE-17	Rohm Semiconductor
1	D4	Diode, Zener, 25 V, 500 mW, SOD-123	MMSZ5253BT1G	On Semiconductor
1	D5	Diode, fast recovery glass passivated, 1 A, 1 kV, DO-41	UF4007-TP	Micro Commercial Co.
1	D6	Diode, dual Schottky, 20 A, 100 V, TO-220	STPS20H100CT	STMicroelectronics
1	D7	Diode, Zener, 10 V, 500 mW, SOD-123	MMSZ5240B	Fairchild Semiconductor
1	D8	Diode, Schottky barrier, 1 A, 30 V, SMini2-F2	MA21D3400L	Panasonic - SSG
1	F1	Fuse, slow blow, 1 A, 250 V, 0.335 inch	38211000410	Littelfuse / Wickmann
1	HS1	Heatsink, TO-220, vertical-mount, 0.5 x 0.750 inch	507302B00000	Aavid Thermalloy
1	HS2	Heatsink, alloy 1110 copper, 0.530 x 1.200 inch	HS001	NH Stamp
1	L1	Inductor, AC line, common choke, 2 7 mH, 1 A, 0.660 x 0.670 inch	54P512-276	Vitec Electronics Corp.
1	L2	Inductor, high current choke, 3.3 µH, 0.276 x 0.288 inch	HCP0703-3R3-R	Coiltronics/Cooper
1	Q1	MOSFET, Nch, 600 V, 6 A, SC-67	2SK3562	Toshiba



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# Table 3. List of Materials for UCC28610EVM-474 (continued)

COUNT	REF DES	DESCRIPTION	PART NUMBER	MFR
1	R1	Resistor, chip, 100 kΩ, 1/10 W, ±1%, 0603	Std	Std
1	R2	Resistor, chip, 20.5 kΩ, 1/10 W, ±1%, 0603	Std	Std
1	R3	Resistor, chip, 51.1 kΩ, 1/10 W, ±1%, 0603	Std	Std
1	R4	Resistor, chip, 64.9 kΩ, 1/10 W, ±1%, 0603	Std	Std
1	R5	Resistor, metal film, 169 k $\Omega$ , 1/2 W, ±1%, 0.300 x 0.100 inch	SFR16S0001693FR500	Vishay/BC Components
1	R6	Resistor, chip, 68.1 kΩ, 1/10 W, ±1%, 0603	Std	Std
3	R7, R8, R9	Resistor, chip, 2.05MΩ, 1/8 W, 150V, ±1%, 0805	CRCW08052M05FKEA	Vishay/Dale
1	R10	Resistor, chip, 15.4 Ω, 1/8 W, ±1%, 0805	Std	Std
1	R11	Resistor, chip, 64.9 kΩ, 1/2 W, ±1%, 2010	Std	Std
1	R12	Resistor, chip, 33.2 Ω, 1 W, ±5%, 2512	Std	Std
1	R13	Resistor, chip, 20.5 Ω, 1/10 W, ±1%, 0603	Std	Std
1	R14	Resistor, chip, 1.00 kΩ, 1/10 W, ±1%, 0603	Std	Std
1	R15	Resistor, chip, 681 Ω, 1/10 W, ±1%, 0603	Std	Std
1	R16	Resistor, chip, 0 Ω, 1/10 W, ±1%, 0603	Std	Std
1	R19	Resistor, metal film, 1.00 kΩ, 1/4 W, ±1%, TH-400	Std	Std
1	T1	Transformer, flyback, 220 µH, PQ20/20	58P6936	Vitec Electronics
1	U1	Green-mode flyback controller, SO-8	UCC28610D	Texas Instruments
1	U2	Optocoupler, CTR 40% - 80%, 70 Vceo, 5000 V <sub>RMS</sub> , DIP6	CNY17F1M	Fairchild Optoelectronics

# 10 References

- 1. UCC28610 Green-Mode Flyback Controller, Datasheet, (TI Literature Number SLUS888)
- 2. Standby and Low Power Measurements, VOLTECHNOTES, VPN 104-054/1, http://www.voltech.com/Downloads/PMAppNotes/Low%20Power%20Standby.pdf



# Appendix A

# A.1 UCC28610EVM-474 Rev. A

The following schematic, board layout, and list of materials apply to the UCC28610EVM-474 Rev. A version of the evaluation module. The Rev. A version of the EVM includes differential mode inductors L2 and L3. Subsequent revisions of the EVM replaced these inductors with a short circuit.

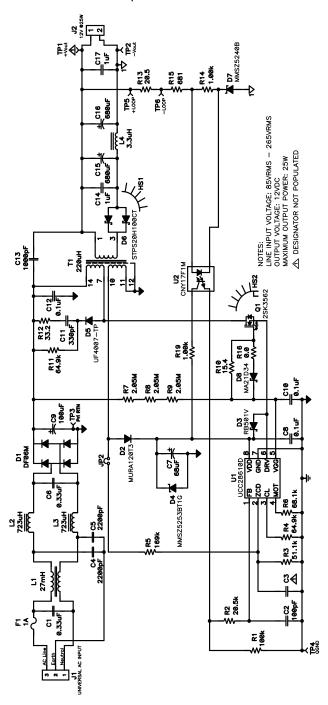


Figure 27. UCC28610EVM-474 Rev. A Schematic



www.ti.com UCC28610EVM-474 Rev. A

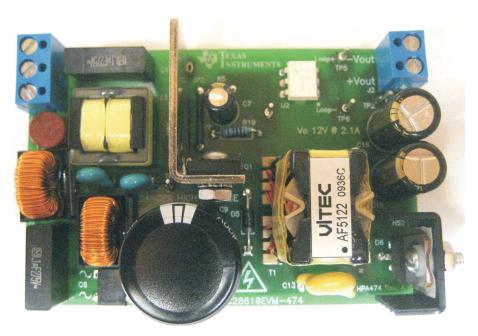


Figure 28. Top Side View of UCC28610EVM-474 Rev. A

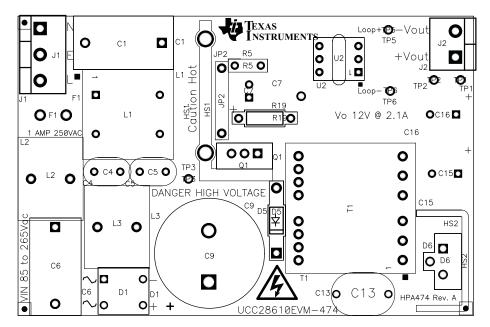


Figure 29. Top Layer Component Placement for UCC28610EVM-474 Rev. A



UCC28610EVM-474 Rev. A www.ti.com

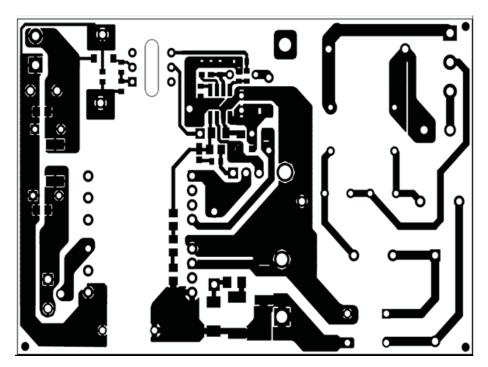


Figure 30. Bottom Layer Routing of UCC28610EVM-474 Rev. A

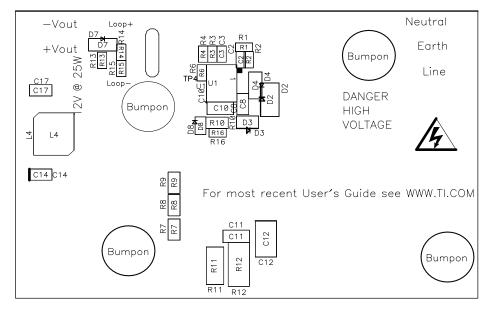


Figure 31. Bottom Layer Component Placement of UCC28610EVM-474 Rev. A



www.ti.com UCC28610EVM-474 Rev. A

# Table 4. Table 4. List of Materials for UCC28610EVM-474 Rev. A

2         C1, C6         Capacitor, film, 0.33 μF, 275VAC, X2, ±20%, 0.690 x 0.374 inch         ECQ-U2A334ML         Panasonic           1         C2         Capacitor, ceramic, 100 pF, 50 V, NP0, ±5%, 0603         Std         Std         Std           0         C3         Capacitor, ceramic, 2200 pF, 250 VAC, X1/V2, ±20%, 013 fx v. 0200 inch         DE2E3KY222MA2BM on muRata         muRata           1         C7         Capacitor, ceramic, 2200 pF, 250 VAC, X1/V2, ±20%, 0.200 inch         EEU-FC1V680         Panasonic           1         C7         Capacitor, ceramic, 0.1 μF, 50 V, X7R, ±10%, 0805         CC0805KRX7R9BB10 on 2.20 fx 25 x 20 mm         Yageo Corporation           1         C9         Capacitor, aluminum electrolytic, 100 μF, 400 VDC, ±20%, 25 x 20 mm         EET-HC2G101BA         Panasonic           1         C10         Capacitor, ceramic, 0.1 μF, 100 V, X7R, ±10%, 0805         Std         Std           1         C11         Capacitor, ceramic, 330 pF, 630 V, COG, NP0, ±56, 1206         Std         Std           1         C12         Capacitor, ceramic, 0.1 μF, 630 V, X7R, ±10%, 0805         Std         Std           1         C13         Capacitor, ceramic, 0.1 μF, 630 V, X7R, ±10%, 0805         Std         Std           2         C14, C17         Capacitor, ceramic, 1 μF, 25 V, X5R, ±10%, 0805         Std         St	COUNT	REF DES	DESCRIPTION	PART NUMBER	MFR
0         C3         Capacitor, ceramic, not populated, 50 V, NP0, ±5%, 0603         Std         Std           2         C4, C5 (optional)         Capacitor, ceramic, 2200 pF, 250 VAC, X1/Y2, ±20%, 0.315 x 0.200 inch         DE2E3KY222MA2BM muRata           1         C7         Capacitor, aluminum electrolytic, 68 μF, 35 V, ±20%, 0.200 inch         EEU-FC1V680         Panasonic           1         C8         Capacitor, ceramic, 0.1 μF, 50 V, X7R, ±10%, 0805         CC0805KRX7R9BB10 Vageo Corporation           1         C9         Capacitor, aluminum electrolytic, 100 μF, 400 VDC, ±20%, 25 x 20 mm         EET-HC2G101BA         Panasonic           1         C10         Capacitor, ceramic, 0.1 μF, 100 V, X7R, ±10%, 1206         Std         Std           1         C11         Capacitor, ceramic, 0.1 μF, 100 V, X7R, ±10%, 1206         Std         Std           1         C12         Capacitor, ceramic, 0.1 μF, 630 V, X7R, ±10%, 1812         C4532X7R2J104K         TDK Corporation           1         C12         Capacitor, ceramic disk, 1000 pF, 250 V, Y1/X1, ±20%, 1812         ECK-ANA102MB         Panasonic           2         C14, C17         Capacitor, ceramic, 1 μF, 25 V, X5R, ±10%, 0805         Std         Std         Std           2         C14, C17         Capacitor, aluminum electrolytic, 680 μF, 25 V, ±20%, 10         EEU-FM1E681         Panasonic	2	C1, C6		ECQ-U2A334ML	Panasonic
2         C4, C5 (optional)         Capacitor, ceramic, 2200 pF, 250 VAC, X1/Y2, ±20%, 0.315 x 0.200 inch         DE2E3KY222MA2BM 01         muRata           1         C7         Capacitor, aluminum electrolytic, 68 μF, 35 V, ±20%, 200 inch         EEU-FC1V680         Panasonic           1         C8         Capacitor, ceramic, 0.1 μF, 50 V, X7R, ±10%, 0805         4         CC0805KRX7R9BB10 Vageo Corporation           1         C9         Capacitor, aluminum electrolytic, 100 μF, 400 VDC, ±20%, 25 x 20 mm         EET.HC2G101BA         Panasonic           1         C10         Capacitor, ceramic, 0.1 μF, 100 V, X7R, ±10%, 1206         Std         Std           1         C11         Capacitor, ceramic, 0.1 μF, 630 V, X7R, ±10%, 1812         C4532X7R2J104K         TDK Corporation           1         C12         Capacitor, ceramic disk, 1000 pF, 250 V, Y1/X1, ±20%, 30, 44 x 0.315 inch         ECK-ANA102MB         Panasonic           1         C13         Capacitor, ceramic, 1 μF, 25 V, X5R, ±10%, 0805         Std         Std         Std           2         C14, C17         Capacitor, aluminum electrolytic, 680 μF, 25 V, ±20%, 10 x 25 mm         EEU-FM16681         Panasonic           1         D1         Diode, bridge, 1 A, 600 V         DF06M         Diodes Inc.           1         D1         Diode, bridge, 1 A, 600 V         MWRA120T3G	1	C2	Capacitor, ceramic, 100 pF, 50 V, NP0, ±5%, 0603	Std	Std
Coptional   0.315 x 0.200 inch   Capacitor, aluminum electrolytic, 68 μF, 35 V, ±20%, 0.200 inch   EEU-FC1V680   Panasonic	0	C3	Capacitor, ceramic, not populated, 50 V, NP0, ±5%, 0603	Std	Std
1 C8 Capacitor, ceramic, 0.1 μF, 50 V, X7R, ±10%, 0805  1 C9 Capacitor, aluminum electrolytic, 100 μF, 400 VDC, ±20%, 25 x 20 mm  1 C10 Capacitor, ceramic, 0.1 μF, 100 V, X7R, ±10%, 1206  1 C11 Capacitor, ceramic, 330 μF, 630 V, C0G, NPO, ±5%, 1206  1 C12 Capacitor, ceramic, 0.1 μF, 630 V, X7R, ±10%, 1812  C13 Capacitor, ceramic, 0.1 μF, 630 V, X7R, ±10%, 1812  C14, C17 Capacitor, ceramic disk, 1000 μF, 250 V, Y1/X1, ±20%, 0.994 x 0.315 inch  C15 Capacitor, ceramic, 1 μF, 25 V, X5R, ±10%, 0805  C16 Capacitor, ceramic, 1 μF, 25 V, X5R, ±10%, 0805  C175, C16 Capacitor, ceramic, 1 μF, 25 V, X5R, ±10%, 0805  C19 C15, C16 Capacitor, aluminum electrolytic, 680 μF, 25 V, ±20%, 10 EEU-FM1E681  D1 Diode, bridge, 1 A, 600 V  DF06M  Diodes Inc.  D2 Diode, ultra fast, 1 A, 200 V, SMA  MURA12013G  On Semiconductor  D3 Diode, Schottky, 100 mA, 40 V, SOD-323  RB501V-40TE-17  Rohm Semiconductor  D4 Diode, Zener, 500 mW, 25 V, SOD-123  MMS25253BT1G  On Semiconductor  D5 Diode, fast recovery glass passivated, 1 A, 1 kV, DO-41  D6 Diode, dual Schottky, 20 A, 100 V, TO-220  TPS20H100CT  STMicroelectronics  TMicroelectronics  TMicroelectronics  MMSZ5240B  Fairchild Semiconductor  B8 Diode, Schottky barrier, 1 A, 30 V, SMini2-F2  MA21D3400L  Panasonic  Littlefluse / Wickmann  HS1 Heatsink, TO-220, vertical mount, 0.5 x 0.750 inch  HS2 Heatsink, alloy 1110 copper, 0.530 x 1.200 inch  HS2 Heatsink, alloy 1110 copper, 0.530 x 1.200 inch  L1 L1 Inductor, AC line, common choke, 27 mH, 1 A, 0.660 x 0.670 inch  L2 L2, L3 Inductor, EMI, 723 μH, 0.620 Ω, ±15%, 11.94 x 15.49 mm  SET-HC2G101BA  Panasonic  CC07D.  Vageo Corporation  EEU-FH1E2010HA  Panasonic  EET-HC2G101BA  Panasonic  Std  Std  Std  Std  Std  Std  Std  St	2				muRata
1 C9 Capacitor, Ceramic, 0.1 μF, 50 V, X/R, ±10%, 0805 1 C9 Capacitor, aluminum electrolytic, 100 μF, 400 VDC, ±20%, 25 x 20 mm 1 C10 Capacitor, ceramic, 0.1 μF, 100 V, X7R, ±10%, 1206 1 C11 Capacitor, ceramic, 330 μF, 630 V, C0G, NP0, ±5%, 1206 1 C12 Capacitor, ceramic, 0.1 μF, 630 V, X7R, ±10%, 1812 C4532X7R2J104K TDK Corporation 1 C13 Capacitor, ceramic disk, 1000 μF, 250 V, Y1/X1, ±20%, 0.394 x 0.315 inch 2 C14, C17 Capacitor, ceramic, 1 μF, 25 V, X5R, ±10%, 0805 2 C14, C17 Capacitor, ceramic, 1 μF, 25 V, X5R, ±10%, 0805 3 Std	1	C7		EEU-FC1V680	Panasonic
1 C10 Capacitor, ceramic, 0.1 μF, 100 V, X7R, ±10%, 1206 Std Std Std  1 C11 Capacitor, ceramic, 330 pF, 630 V, C0G, NPO, ±5%, 1206 Std Std Std  1 C12 Capacitor, ceramic, 0.1 μF, 630 V, X7R, ±10%, 1812 C4532X7R2J104K TDK Corporation  1 C13 Capacitor, ceramic disk, 1000 pF, 250 V, Y1/X1, ±20%, 0.394 x 0.315 inch  2 C14, C17 Capacitor, ceramic, 1 μF, 25 V, X5R, ±10%, 0805 Std Std Std Std  2 C15, C16 Capacitor, aluminum electrolytic, 680 μF, 25 V, ±20%, 10 EEU-FM1E681 Panasonic  1 D1 Diode, bridge, 1 A, 600 V DF06M Diodes Inc.  1 D2 Diode, ultra fast, 1 A, 200 V, SMA MURA120T3G On Semiconductor  1 D3 Diode, Schottky, 100 mA, 40 V, SOD-323 RB501V-40TE-17 Rohm Semiconductor  1 D4 Diode, Zener, 500 mW, 25 V, SOD-123 MMSZ5253BT1G On Semiconductor  1 D5 Diode, fast recovery glass passivated, 1 A, 1 kV, DO-41 UF4007-TP Micro Commercial Co.  1 D6 Diode, dual Schottky, 20 A, 100 V, TO-220 STPS20H100CT STMicroelectronics  1 D7 Diode, Zener, 10 V, 500 mW, SOD-123 MMSZ5240B Fairchild Semiconductor  1 D8 Diode, Schottky barrier, 1 A, 30 V, SMini2-F2 MA21D3400L Panasonic - SSG  1 F1 Fuse, slow blow, 1 A, 250 V, 0.335 inch 38211000410 Littelfuse / Wickmann  1 HS1 Heatsink, TO-220, vertical mount, 0.5 x 0.750 inch 507302B00000 Aavid Thermalloy  1 HS2 Heatsink, alloy 1110 copper, 0.530 x 1.200 inch HS001 NH Stamp  1 L1 Inductor, AC line, common choke, 27 mH, 1 A, 0.660 x 0.670 inch  1 L4 Inductor, high current choke, 23 μH, 0.276 x 0.288 inch HCP0703-3R3-R Coiltronics/Cooper	1	C8	Capacitor, ceramic, 0.1 µF, 50 V, X7R, ±10%, 0805		Yageo Corporation
1 C11 Capacitor, ceramic, 330 pF, 630 V, C0G, NPO, ±5%, 1206 Std Std DC12 Capacitor, ceramic, 0.1 μF, 630 V, X7R, ±10%, 1812 C4532X7R2J104K TDK Corporation  1 C13 Capacitor, ceramic disk, 1000 pF, 250 V, Y1/X1, ±20%, 0.394 x 0.315 inch  2 C14, C17 Capacitor, ceramic, 1 μF, 25 V, X5R, ±10%, 0805 Std Std Std  2 C15, C16 Capacitor, ceramic, 1 μF, 25 V, X5R, ±10%, 0805 Std Std Std  2 C15, C16 Capacitor, aluminum electrolytic, 680 μF, 25 V, ±20%, 10 μEU-FM1E681 Panasonic  1 D1 Diode, bridge, 1 A, 600 V DF06M Diodes Inc.  1 D2 Diode, ultra fast, 1 A, 200 V, SMA MURA120T3G On Semiconductor  1 D3 Diode, Schottky, 100 mA, 40 V, SOD-323 RB501V-40TE-17 Rohm Semiconductor  1 D4 Diode, Zener, 500 mW, 25 V, SOD-123 MMSZ5253BT1G On Semiconductor  1 D5 Diode, fast recovery glass passivated, 1 A, 1 kV, DO-41 UF4007-TP Micro Commercial Co.  1 D6 Diode, dual Schottky, 20 A, 100 V, TO-220 STPS20H100CT STMicroelectronics  1 D7 Diode, Zener, 10 V, 500 mW, SOD-123 MMSZ5240B Fairchild Semiconductor  1 D8 Diode, Schottky barrier, 1 A, 30 V, SMini2-F2 MA21D3400L Panasonic - SSG  1 F1 Fuse, slow blow, 1 A, 250 V, 0.335 inch 38211000410 Littelfuse / Wickmann  1 HS1 Heatsink, TO-220, vertical mount, 0.5 x 0.750 inch 507302B00000 Aavid Thermalloy  1 HS2 Heatsink, alloy 1110 copper, 0.530 x 1.200 inch HS001 NH Stamp  1 L1 Inductor, AC line, common choke, 27 mH, 1 A, 0.660 x 0.670 inch Unductor, EMI, 723 μH, 0.620 Ω, ±15%, 11.94 x 15.49 mm 54P2986 Vitec Electronics Corp.  1 L4 Inductor, high current choke, 3.3 μH, 0.276 x 0.288 inch HCP0703-3R3-R Coiltronics/Cooper	1	C9		EET-HC2G101BA	Panasonic
1 C12 Capacitor, ceramic, 0.1 μF, 630 V, X7R, ±10%, 1812 C4532X7R2J104K TDK Corporation 1 C13 Capacitor, ceramic disk, 1000 pF, 250 V, Y1/X1, ±20%, 0.394 x 0.315 inch 2 C14, C17 Capacitor, ceramic, 1 μF, 25 V, X5R, ±10%, 0805 Std Std Std 2 C15, C16 Capacitor, aluminum electrolytic, 680 μF, 25 V, ±20%, 10 μ EEU-FM1E681 Panasonic 1 D1 Diode, bridge, 1 A, 600 V DF06M Diodes Inc. 1 D2 Diode, ultra fast, 1 A, 200 V, SMA MURA120T3G On Semiconductor 1 D3 Diode, Schottky, 100 mA, 40 V, SOD-323 RB501V-40TE-17 Rohm Semiconductor 1 D4 Diode, Zener, 500 mW, 25 V, SOD-123 MMSZ5253BT1G On Semiconductor 1 D5 Diode, fast recovery glass passivated, 1 A, 1 kV, DO-41 UF4007-TP Micro Commercial Co. 1 D6 Diode, dual Schottky, 20 A, 100 V, TO-220 STPS20H100CT STMicroelectronics 1 D7 Diode, Zener, 10 V, 500 mW, SOD-123 MMSZ5240B Fairchild Semiconductor 1 D8 Diode, Schottky barrier, 1 A, 30 V, SMini2-F2 MA21D3400L Panasonic - SSG 1 F1 Fuse, slow blow, 1 A, 250 V, 0.335 inch 38211000410 Littelfuse / Wickmann 1 HS1 Heatsink, TO-220, vertical mount, 0.5 x 0.750 inch 507302B00000 Aavid Thermalloy 1 HS2 Heatsink, alloy 1110 copper, 0.530 x 1.200 inch HS001 NH Stamp 1 L1 Inductor, AC line, common choke, 27 mH, 1 A, 0.660 x 0.670 inch Inductor, EMI, 723 μH, 0.620 Ω, ±15%, 11.94 x 15.49 mm 54P2986 Vitec Electronics Corp. 2 L2, L3 Inductor, high current choke, 3.3 μH, 0.276 x 0.288 inch HCP0703-3R3-R Coiltronics/Cooper	1	C10	Capacitor, ceramic, 0.1 µF, 100 V, X7R, ±10%, 1206	Std	Std
1 C13 Capacitor, ceramic disk, 1000 pF, 250 V, Y1/X1, ±20%, 0.394 x 0.315 inch 2 C14, C17 Capacitor, ceramic, 1 μF, 25 V, X5R, ±10%, 0805 3td Std Std  2 C15, C16 Capacitor, aluminum electrolytic, 680 μF, 25 V, ±20%, 10 EEU-FM1E681 Panasonic  1 D1 Diode, bridge, 1 A, 600 V DF06M Diodes Inc.  1 D2 Diode, ultra fast, 1 A, 200 V, SMA MURA120T3G On Semiconductor  1 D3 Diode, Schottky, 100 mA, 40 V, SOD-323 RB501V-40TE-17 Rohm Semiconductor  1 D4 Diode, Zener, 500 mW, 25 V, SOD-123 MMSZ5253BT1G On Semiconductor  1 D5 Diode, fast recovery glass passivated, 1 A, 1 kV, DO-41 UF4007-TP Micro Commercial Co.  1 D6 Diode, dual Schottky, 20 A, 100 V, TO-220 STPS20H100CT STMicroelectronics  1 D7 Diode, Zener, 10 V, 500 mW, SOD-123 MMSZ5240B Fairchild Semiconductor  1 D8 Diode, Schottky barrier, 1 A, 30 V, SMini2-F2 MA21D3400L Panasonic - SSG  1 F1 Fuse, slow blow, 1 A, 250 V, 0.335 inch 38211000410 Litteffuse / Wickmann  1 HS1 Heatsink, TO-220, vertical mount, 0.5 x 0.750 inch 507302B00000 Aavid Thermalloy  1 HS2 Heatsink, alloy 1110 copper, 0.530 x 1.200 inch HS001 NH Stamp  1 L1 Inductor, AC line, common choke, 27 mH, 1 A, 0.660 x 0.670 inch Vitec Electronics Corp.  2 L2, L3 Inductor, EMI, 723 μH, 0.620 Ω, ±15%, 11.94 x 15.49 mm 54P2986 Vitec Electronics Corp.	1	C11	Capacitor, ceramic, 330 pF, 630 V, C0G, NP0, ±5%, 1206	Std	Std
1         C13         0.394 x 0.315 inch         ECK-ANATOZNIB         Pariasonic           2         C14, C17         Capacitor, ceramic, 1 μF, 25 V, X5R, ±10%, 0805         Std         Std           2         C15, C16         Capacitor, aluminum electrolytic, 680 μF, 25 V, ±20%, 10 x 25 mm         EEU-FM1E681         Panasonic           1         D1         Diode, bridge, 1 A, 600 V         DF06M         Diodes Inc.           1         D2         Diode, ultra fast, 1 A, 200 V, SMA         MURA12073G         On Semiconductor           1         D3         Diode, Schottky, 100 mA, 40 V, SOD-323         RB501V-40TE-17         Rohm Semiconductor           1         D4         Diode, Schottky, 20 M, 40 V, SOD-123         MMSZ5253BT1G         On Semiconductor           1         D5         Diode, fast recovery glass passivated, 1 A, 1 kV, DO-41         UF4007-TP         Micro Commercial Co.           1         D6         Diode, dual Schottky, 20 A, 100 V, TO-220         STPS20H100CT         STMicroelectronics           1         D7         Diode, Zener, 10 V, 500 mW, SOD-123         MMSZ5240B         Faircihild Semiconductor           1         D8         Diode, Schottky barrier, 1 A, 30 V, SMini2-F2         MA21D3400L         Panasonic - SSG           1         F1         Fuse, slow blow, 1 A, 250 V, 0.3	1	C12	Capacitor, ceramic, 0.1 µF, 630 V, X7R, ±10%, 1812	C4532X7R2J104K	TDK Corporation
2 C15, C16 Capacitor, aluminum electrolytic, 680 μF, 25 V, ±20%, 10 x 25 mm  D1 Diode, bridge, 1 A, 600 V  D506M  Diodes Inc.  D2 Diode, ultra fast, 1 A, 200 V, SMA  MURA120T3G  On Semiconductor  D3 Diode, Schottky, 100 mA, 40 V, SOD-323  RB501V-40TE-17  Rohm Semiconductor  D4 Diode, Zener, 500 mW, 25 V, SOD-123  MMSZ5253BT1G  On Semiconductor  D5 Diode, fast recovery glass passivated, 1 A, 1 kV, DO-41  D6 Diode, dual Schottky, 20 A, 100 V, TO-220  STPS20H100CT  STMicroelectronics  D7 Diode, Zener, 10 V, 500 mW, SOD-123  MMSZ5240B  Fairchild Semiconductor  D8 Diode, Schottky barrier, 1 A, 30 V, SMini2-F2  MA21D3400L  Panasonic - SSG  F1 F1 Fuse, slow blow, 1 A, 250 V, 0.335 inch  HS1 Heatsink, TO-220, vertical mount, 0.5 x 0.750 inch  HS2 Heatsink, alloy 1110 copper, 0.530 x 1.200 inch  HS01 Inductor, AC line, common choke, 27 mH, 1 A, 0.660 x 0.670 inch  L1 Inductor, EMI, 723 μH, 0.620 Ω, ±15%, 11.94 x 15.49 mm  L4 Inductor, high current choke, 3.3 μH, 0.276 x 0.288 inch  HCP0703-3R3-R  Coiltronics/Cooper	1	C13		ECK-ANA102MB	Panasonic
2         C15, C16         x 25 mm         EEU-FMTEO81         Panasonic           1         D1         Diode, bridge, 1 A, 600 V         DF06M         Diodes Inc.           1         D2         Diode, ultra fast, 1 A, 200 V, SMA         MURA120T3G         On Semiconductor           1         D3         Diode, Schottky, 100 mA, 40 V, SOD-323         RB501V-40TE-17         Rohm Semiconductor           1         D4         Diode, Zener, 500 mW, 25 V, SOD-123         MMSZ5253BT1G         On Semiconductor           1         D5         Diode, fast recovery glass passivated, 1 A, 1 kV, DO-41         UF4007-TP         Micro Commercial Co.           1         D6         Diode, dual Schottky, 20 A, 100 V, TO-220         STPS20H100CT         STMicroelectronics           1         D7         Diode, Zener, 10 V, 500 mW, SOD-123         MMSZ5240B         Fairchild Semiconductor           1         D8         Diode, Schottky barrier, 1 A, 30 V, SMini2-F2         MA21D3400L         Panasonic - SSG           1         F1         Fuse, slow blow, 1 A, 250 V, 0.335 inch         38211000410         Littelfuse / Wickmann           1         HS1         Heatsink, TO-220, vertical mount, 0.5 x 0.750 inch         507302B00000         Aavid Thermalloy           1         HS2         Heatsink, alloy 1110 copper, 0.530 x 1.20	2	C14, C17	Capacitor, ceramic, 1 µF, 25 V, X5R, ±10%, 0805	Std	Std
1 D2 Diode, ultra fast, 1 A, 200 V, SMA MURA120T3G On Semiconductor 1 D3 Diode, Schottky, 100 mA, 40 V, SOD-323 RB501V-40TE-17 Rohm Semiconductor 1 D4 Diode, Zener, 500 mW, 25 V, SOD-123 MMSZ5253BT1G On Semiconductor 1 D5 Diode, fast recovery glass passivated, 1 A, 1 kV, DO-41 UF4007-TP Micro Commercial Co. 1 D6 Diode, dual Schottky, 20 A, 100 V, TO-220 STPS20H100CT STMicroelectronics 1 D7 Diode, Zener, 10 V, 500 mW, SOD-123 MMSZ5240B Fairchild Semiconductor 1 D8 Diode, Schottky barrier, 1 A, 30 V, SMini2-F2 MA21D3400L Panasonic - SSG 1 F1 Fuse, slow blow, 1 A, 250 V, 0.335 inch 38211000410 Littelfuse / Wickmann 1 HS1 Heatsink, TO-220, vertical mount, 0.5 x 0.750 inch 507302B00000 Aavid Thermalloy 1 HS2 Heatsink, alloy 1110 copper, 0.530 x 1.200 inch HS001 NH Stamp 1 L1 Inductor, AC line, common choke, 27 mH, 1 A, 0.660 x 0.670 inch Unductor, EMI, 723 μH, 0.620 Ω, ±15%, 11.94 x 15.49 mm 54P2986 Vitec Electronics Corp. 1 L4 Inductor, high current choke, 3.3 μH, 0.276 x 0.288 inch HCP0703-3R3-R Coiltronics/Cooper	2	C15, C16		EEU-FM1E681	Panasonic
1 D3 Diode, Schottky, 100 mA, 40 V, SOD-323 RB501V-40TE-17 Rohm Semiconductor 1 D4 Diode, Zener, 500 mW, 25 V, SOD-123 MMSZ5253BT1G On Semiconductor 1 D5 Diode, fast recovery glass passivated, 1 A, 1 kV, DO-41 UF4007-TP Micro Commercial Co. 1 D6 Diode, dual Schottky, 20 A, 100 V, TO-220 STPS20H100CT STMicroelectronics 1 D7 Diode, Zener, 10 V, 500 mW, SOD-123 MMSZ5240B Fairchild Semiconductor 1 D8 Diode, Schottky barrier, 1 A, 30 V, SMini2-F2 MA21D3400L Panasonic - SSG 1 F1 Fuse, slow blow, 1 A, 250 V, 0.335 inch 38211000410 Littelfuse / Wickmann 1 HS1 Heatsink, TO-220, vertical mount, 0.5 x 0.750 inch 507302B00000 Aavid Thermalloy 1 HS2 Heatsink, alloy 1110 copper, 0.530 x 1.200 inch HS001 NH Stamp 1 L1 Inductor, AC line, common choke, 27 mH, 1 A, 0.660 x 0.670 inch Vitec Electronics Corp. 2 L2, L3 Inductor, EMI, 723 μH, 0.620 Ω, ±15%, 11.94 x 15.49 mm 54P2986 Vitec Electronics Corp. 1 Inductor, high current choke, 3.3 μH, 0.276 x 0.288 inch HCP0703-3R3-R Coiltronics/Cooper	1	D1	Diode, bridge, 1 A, 600 V	DF06M	Diodes Inc.
1 D4 Diode, Zener, 500 mW, 25 V, SOD-123 MMSZ5253BT1G On Semiconductor 1 D5 Diode, fast recovery glass passivated, 1 A, 1 kV, DO-41 UF4007-TP Micro Commercial Co. 1 D6 Diode, dual Schottky, 20 A, 100 V, TO-220 STPS20H100CT STMicroelectronics 1 D7 Diode, Zener, 10 V, 500 mW, SOD-123 MMSZ5240B Fairchild Semiconductor 1 D8 Diode, Schottky barrier, 1 A, 30 V, SMini2-F2 MA21D3400L Panasonic - SSG 1 F1 Fuse, slow blow, 1 A, 250 V, 0.335 inch 38211000410 Littelfuse / Wickmann 1 HS1 Heatsink, TO-220, vertical mount, 0.5 x 0.750 inch 507302B00000 Aavid Thermalloy 1 HS2 Heatsink, alloy 1110 copper, 0.530 x 1.200 inch HS001 NH Stamp 1 L1 Inductor, AC line, common choke, 27 mH, 1 A, 0.660 x 0.670 inch Uitec Electronics Corp. 2 L2, L3 Inductor, EMI, 723 μH, 0.620 Ω, ±15%, 11.94 x 15.49 mm 54P2986 Vitec Electronics Corp. 1 L4 Inductor, high current choke, 3.3 μH, 0.276 x 0.288 inch HCP0703-3R3-R Coiltronics/Cooper	1	D2	Diode, ultra fast, 1 A, 200 V, SMA	MURA120T3G	On Semiconductor
1 D5 Diode, fast recovery glass passivated, 1 A, 1 kV, DO-41 UF4007-TP Micro Commercial Co. 1 D6 Diode, dual Schottky, 20 A, 100 V, TO-220 STPS20H100CT STMicroelectronics 1 D7 Diode, Zener, 10 V, 500 mW, SOD-123 MMSZ5240B Fairchild Semiconductor 1 D8 Diode, Schottky barrier, 1 A, 30 V, SMini2-F2 MA21D3400L Panasonic - SSG 1 F1 Fuse, slow blow, 1 A, 250 V, 0.335 inch 38211000410 Littelfuse / Wickmann 1 HS1 Heatsink, TO-220, vertical mount, 0.5 x 0.750 inch 507302B00000 Aavid Thermalloy 1 HS2 Heatsink, alloy 1110 copper, 0.530 x 1.200 inch HS001 NH Stamp 1 L1 Inductor, AC line, common choke, 27 mH, 1 A, 0.660 x 0.670 inch Vitec Electronics Corp. 2 L2, L3 Inductor, EMI, 723 μH, 0.620 Ω, ±15%, 11.94 x 15.49 mm 54P2986 Vitec Electronics Corp. 1 L4 Inductor, high current choke, 3.3 μH, 0.276 x 0.288 inch HCP0703-3R3-R Coiltronics/Cooper	1	D3	Diode, Schottky, 100 mA, 40 V, SOD-323	RB501V-40TE-17	Rohm Semiconductor
1 D6 Diode, dual Schottky, 20 A, 100 V, TO-220 STPS20H100CT STMicroelectronics 1 D7 Diode, Zener, 10 V, 500 mW, SOD-123 MMSZ5240B Fairchild Semiconductor 1 D8 Diode, Schottky barrier, 1 A, 30 V, SMini2-F2 MA21D3400L Panasonic - SSG 1 F1 Fuse, slow blow, 1 A, 250 V, 0.335 inch 38211000410 Littelfuse / Wickmann 1 HS1 Heatsink, TO-220, vertical mount, 0.5 x 0.750 inch 507302B00000 Aavid Thermalloy 1 HS2 Heatsink, alloy 1110 copper, 0.530 x 1.200 inch HS001 NH Stamp 1 L1 Inductor, AC line, common choke, 27 mH, 1 A, 0.660 x 0.670 inch Vitec Electronics Corp. 2 L2, L3 Inductor, EMI, 723 μH, 0.620 Ω, ±15%, 11.94 x 15.49 mm 54P2986 Vitec Electronics Corp. 1 L4 Inductor, high current choke, 3.3 μH, 0.276 x 0.288 inch HCP0703-3R3-R Coiltronics/Cooper	1	D4	Diode, Zener, 500 mW, 25 V, SOD-123	MMSZ5253BT1G	On Semiconductor
1 D7 Diode, Zener, 10 V, 500 mW, SOD-123 MMSZ5240B Fairchild Semiconductor  1 D8 Diode, Schottky barrier, 1 A, 30 V, SMini2-F2 MA21D3400L Panasonic - SSG  1 F1 Fuse, slow blow, 1 A, 250 V, 0.335 inch 38211000410 Littelfuse / Wickmann  1 HS1 Heatsink, TO-220, vertical mount, 0.5 x 0.750 inch 507302B00000 Aavid Thermalloy  1 HS2 Heatsink, alloy 1110 copper, 0.530 x 1.200 inch HS001 NH Stamp  1 L1 Inductor, AC line, common choke, 27 mH, 1 A, 0.660 x 0.670 inch S4P512-276 Vitec Electronics Corp.  2 L2, L3 Inductor, EMI, 723 μH, 0.620 Ω, ±15%, 11.94 x 15.49 mm 54P2986 Vitec Electronics Corp.  1 L4 Inductor, high current choke, 3.3 μH, 0.276 x 0.288 inch HCP0703-3R3-R Coiltronics/Cooper	1	D5	Diode, fast recovery glass passivated, 1 A, 1 kV, DO-41	UF4007-TP	Micro Commercial Co.
1 D7 Diode, Zener, 10 V, 500 mW, SOD-123 MMSZ5240B Semiconductor  1 D8 Diode, Schottky barrier, 1 A, 30 V, SMini2-F2 MA21D3400L Panasonic - SSG  1 F1 Fuse, slow blow, 1 A, 250 V, 0.335 inch 38211000410 Littelfuse / Wickmann  1 HS1 Heatsink, TO-220, vertical mount, 0.5 x 0.750 inch 507302B00000 Aavid Thermalloy  1 HS2 Heatsink, alloy 1110 copper, 0.530 x 1.200 inch HS001 NH Stamp  1 L1 Inductor, AC line, common choke, 27 mH, 1 A, 0.660 x 0.670 inch 54P512-276 Vitec Electronics Corp.  2 L2, L3 Inductor, EMI, 723 μH, 0.620 Ω, ±15%, 11.94 x 15.49 mm 54P2986 Vitec Electronics Corp.  1 L4 Inductor, high current choke, 3.3 μH, 0.276 x 0.288 inch HCP0703-3R3-R Coiltronics/Cooper	1	D6	Diode, dual Schottky, 20 A, 100 V, TO-220	STPS20H100CT	STMicroelectronics
1 F1 Fuse, slow blow, 1 A, 250 V, 0.335 inch 38211000410 Littelfuse / Wickmann HS1 Heatsink, TO-220, vertical mount, 0.5 x 0.750 inch 507302B00000 Aavid Thermalloy Heatsink, alloy 1110 copper, 0.530 x 1.200 inch HS001 NH Stamp  1 L1 Inductor, AC line, common choke, 27 mH, 1 A, 0.660 x 0.670 inch 54P512-276 Vitec Electronics Corp.  2 L2, L3 Inductor, EMI, 723 μH, 0.620 Ω, ±15%, 11.94 x 15.49 mm 54P2986 Vitec Electronics Corp.  1 L4 Inductor, high current choke, 3.3 μH, 0.276 x 0.288 inch HCP0703-3R3-R Coiltronics/Cooper	1	D7	Diode, Zener, 10 V, 500 mW, SOD-123	MMSZ5240B	
1 HS1 Heatsink, TO-220, vertical mount, 0.5 x 0.750 inch 507302B00000 Aavid Thermalloy 1 HS2 Heatsink, alloy 1110 copper, 0.530 x 1.200 inch HS001 NH Stamp 1 L1 Inductor, AC line, common choke, 27 mH, 1 A, 0.660 x 0.670 inch 54P512-276 Vitec Electronics Corp. 2 L2, L3 Inductor, EMI, 723 μH, 0.620 Ω, ±15%, 11.94 x 15.49 mm 54P2986 Vitec Electronics Corp. 1 L4 Inductor, high current choke, 3.3 μH, 0.276 x 0.288 inch HCP0703-3R3-R Coiltronics/Cooper	1	D8	Diode, Schottky barrier, 1 A, 30 V, SMini2-F2	MA21D3400L	Panasonic - SSG
1 HS2 Heatsink, alloy 1110 copper, 0.530 x 1.200 inch HS001 NH Stamp  1 L1 Inductor, AC line, common choke, 27 mH, 1 A, 0.660 x 0.670 inch 54P512-276 Vitec Electronics Corp.  2 L2, L3 Inductor, EMI, 723 μH, 0.620 Ω, ±15%, 11.94 x 15.49 mm 54P2986 Vitec Electronics Corp.  1 L4 Inductor, high current choke, 3.3 μH, 0.276 x 0.288 inch HCP0703-3R3-R Coiltronics/Cooper	1	F1	Fuse, slow blow, 1 A, 250 V, 0.335 inch	38211000410	Littelfuse / Wickmann
1 L1 Inductor, AC line, common choke, 27 mH, 1 A, 0.660 x Corp.  2 L2, L3 Inductor, EMI, 723 μH, 0.620 Ω, ±15%, 11.94 x 15.49 mm 54P2986 Vitec Electronics Corp.  1 L4 Inductor, high current choke, 3.3 μH, 0.276 x 0.288 inch HCP0703-3R3-R Coiltronics/Cooper	1	HS1	Heatsink, TO-220, vertical mount, 0.5 x 0.750 inch	507302B00000	Aavid Thermalloy
1 L1 0.670 inch S4P512-276 Corp. 2 L2, L3 Inductor, EMI, 723 μH, 0.620 Ω, ±15%, 11.94 x 15.49 mm 54P2986 Vitec Electronics Corp. 1 L4 Inductor, high current choke, 3.3 μH, 0.276 x 0.288 inch HCP0703-3R3-R Coiltronics/Cooper	1	HS2	Heatsink, alloy 1110 copper, 0.530 x 1.200 inch	HS001	NH Stamp
2 L2, L3 Inductor, EMI, 723 μH, 0.620 Ω, ±15%, 11.94 x 15.49 mm 54P2986 Corp.  1 L4 Inductor, high current choke, 3.3 μH, 0.276 x 0.288 inch HCP0703-3R3-R Coiltronics/Cooper	1	L1		54P512-276	
, J	2	L2, L3	Inductor, EMI, 723 $\mu$ H, 0.620 $\Omega$ , ±15%, 11.94 x 15.49 mm	54P2986	
1 Q1 MOSFET, N-channel, 600 V, 6A, SC-67 2SK3562 Toshiba	1	L4	Inductor, high current choke, 3.3 µH, 0.276 x 0.288 inch	HCP0703-3R3-R	Coiltronics/Cooper
	1	Q1	MOSFET, N-channel, 600 V, 6A, SC-67	2SK3562	Toshiba



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# Table 4. Table 4. List of Materials for UCC28610EVM-474 Rev. A (continued)

COUNT	REF DES	DESCRIPTION	PART NUMBER	MFR
1	R1	Resistor, chip, 100 kΩ, 1/10 W, ±1%, 0603	Std	Std
1	R2	Resistor, chip, 20.5 kΩ, 1/10 W, ±1%, 0603	Std	Std
1	R3	Resistor, chip, 51.1 kΩ, 1/10 W, ±1%, 0603	Std	Std
1	R4	Resistor, chip, 64.9 kΩ, 1/10 W, ±1%, 0603	Std	Std
1	R5	Resistor, metal film, 169 k $\Omega$ , 1/2 W, ±1%, 0.300 x 0.100 inch	SFR16S0001693FR5 00	Vishay/BC Components
1	R6	Resistor, chip, 68.1 kΩ, 1/10 W, ±1%, 0603	Std	Std
3	R7, R8, R9	Resistor, chip, 2.05 MΩ, 1/8 W, 150 V, ±1%, 0805	CRCW08052M05FKE A	Vishay/Dale
1	R10	Resistor, chip, 15.4 W, 1/8 W, ±1%, 0805	Std	Std
1	R11	Resistor, chip, 64.9 kΩ, 1/2 W, ±1%, 2010	Std	Std
1	R12	Resistor, chip, 33.2 Ω, 1 W, ±5%, 2512	Std	Std
1	R13	Resistor, chip, 20.5 Ω, 1/10 W, ±1%, 0603	Std	Std
1	R14	Resistor, chip, 1.00 kΩ, 1/10 W, ±1%, 0603	Std	Std
1	R15	Resistor, chip, 681 Ω, 1/10 W, ±1%, 0603	Std	Std
1	R16	Resistor, chip, 0 Ω, 1/10 W, ±1%, 0603	Std	Std
1	R19	Resistor, metal film, 1.00 kΩ, 1/4 W, ±1%, TH-400	Std	Std
1	T1	Transformer, flyback, 220 µH, PQ20/20	58P6936	Vitec Electronics
1	U1	Green-Mode Flyback Controller, SO-8	UCC28610D	Texas Instruments
1	U2	Optocoupler, CTR 40% - 80%, 70 Vceo, 5000Vrms, DIP6	CNY17F1M	Fairchild Optoelectronics



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It is important to operate this EVM within the input voltage range of 85  $V_{AC}$  to 265  $V_{AC}$  and the output voltage of 12 V .

Exceeding the specified input range may cause unexpected operation and/or irreversible damage to the EVM. If there are questions concerning the input range, please contact a TI field representative prior to connecting the input power.

Applying loads outside of the specified output range may result in unintended operation and/or possible permanent damage to the EVM. Please consult the EVM User's Guide prior to connecting any load to the EVM output. If there is uncertainty as to the load specification, please contact a TI field representative.

During normal operation, some circuit components may have case temperatures greater than 60 °C. The EVM is designed to operate properly with certain components above as long as the input and output ranges are maintained. These components include but are not limited to linear regulators, switching transistors, pass transistors, and current sense resistors. These types of devices can be identified using the EVM schematic located in the EVM User's Guide. When placing measurement probes near these devices during operation, please be aware that these devices may be very warm to the touch.

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